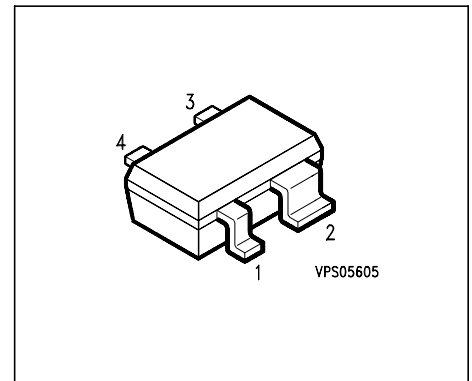


Silicon Schottky Diodes

Preliminary data

- General-purpose diodes for high-speed switching
- Circuit protection
- Voltage clamping
- High-level detection and mixing



ESD: ElectroStatic Discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration				Package
BAS70-07W	77s	Q62702-A1186	1 = C1	2 = C2	3 = A2	4 = A1	SOT-343

Maximum Ratings

Parameter	Symbol	Values	Unit
Diode reverse voltage	V_R	70	V
Forward current	I_F	70	mA
Surge forward current ($t \leq 10\text{ms}$)	I_{FSM}	100	
Total Power dissipation $T_S \leq 91^\circ\text{C}$	P_{tot}	250	mW
Operating temperature range	T_{op}	- 55 ... + 150	$^\circ\text{C}$
Storage temperature	T_{stg}	- 55 ... + 150	

Thermal Resistance

Junction ambient ¹⁾	R_{thJA}	≤ 285	K/W
Junction - soldering point	R_{thJS}	≤ 145	

1) Package mounted on epoxy pcb 40mm x 40mm x 1.5mm / 0.5cm² Cu

Electrical Characteristics at $T_A=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics per Diode

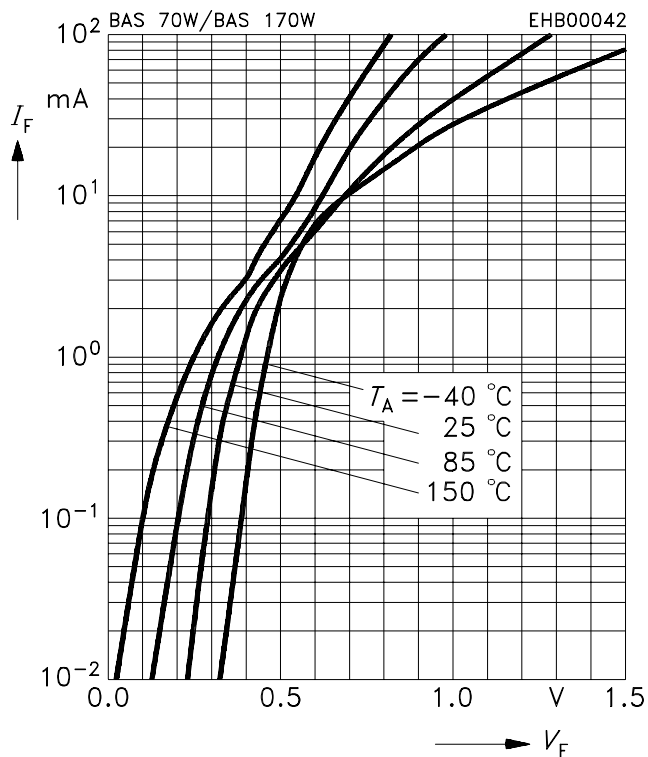
Breakdown voltage $I_{(BR)} = 10 \mu\text{A}$	$V_{(BR)}$	70	-	-	V
Forward voltage $I_F = 1 \text{ mA}$	V_F	300	375	410	
$I_F = 10 \text{ mA}$		600	705	750	
$I_F = 15 \text{ mA}$		750	880	1000	
Reverse current $V_R = 50 \text{ V}$	I_R	-	-	0.1	μA
$V_R = 70 \text{ V}$		-	-	10	

AC characteristics

Diode capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	-	1.5	2	pF
Charge carrier life time $I_F = 25 \text{ mA}$	τ	-	-	100	ps
Forward resistance $I_F = 10 \text{ mA}, f = 10 \text{ kHz}$	r_f	-	34	-	Ω
Series inductance	L_S	-	2	-	nH

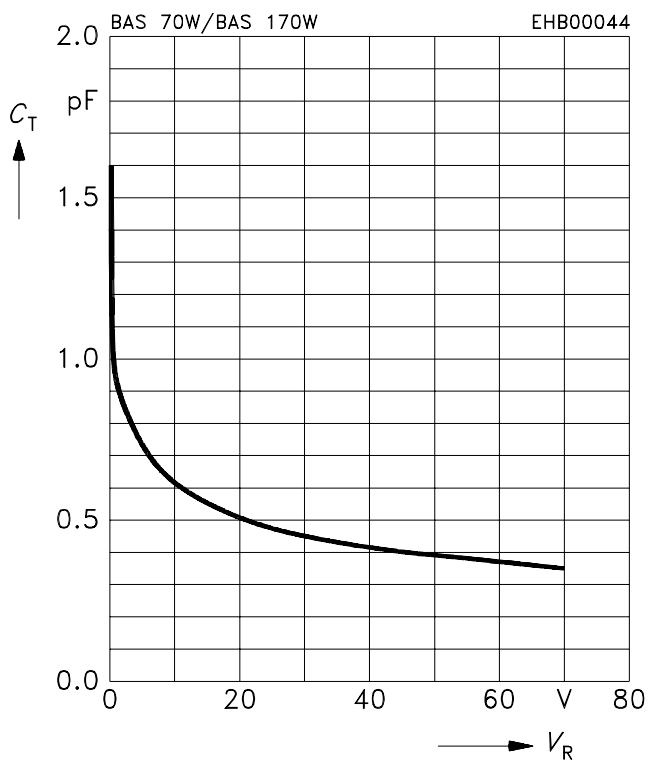
Forward current $I_F = f(V_F)$

T_A = parameter



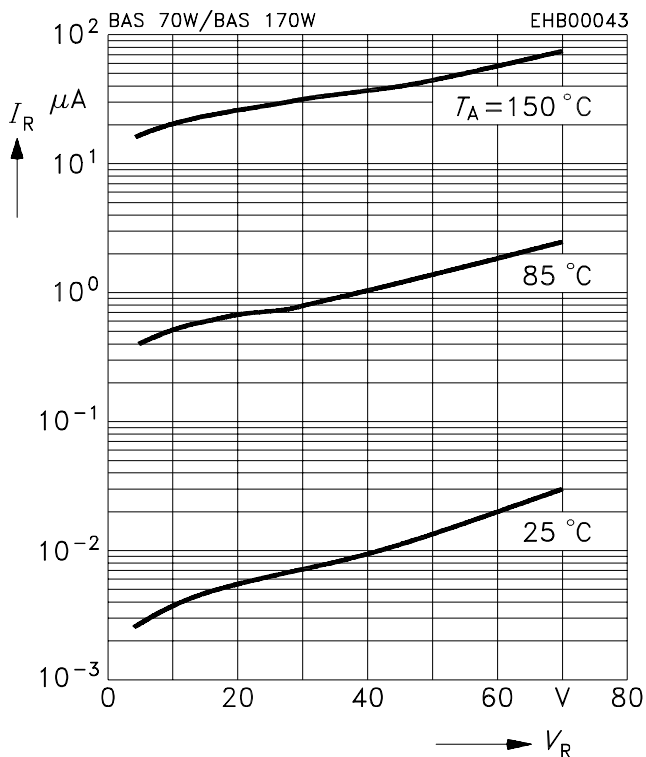
Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



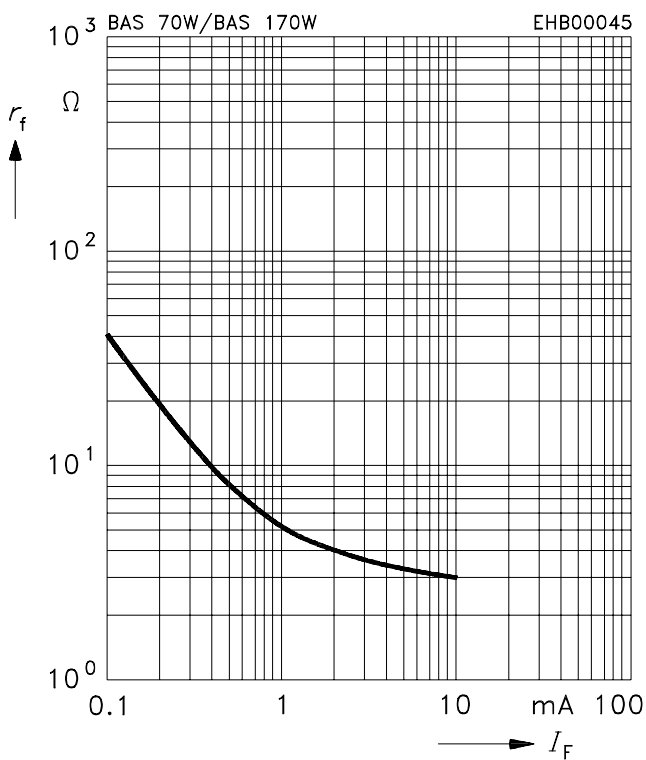
Reverse current $I_R = f(V_R)$

T_A = Parameter



Differential forward resistance $R_F = f(I_F)$

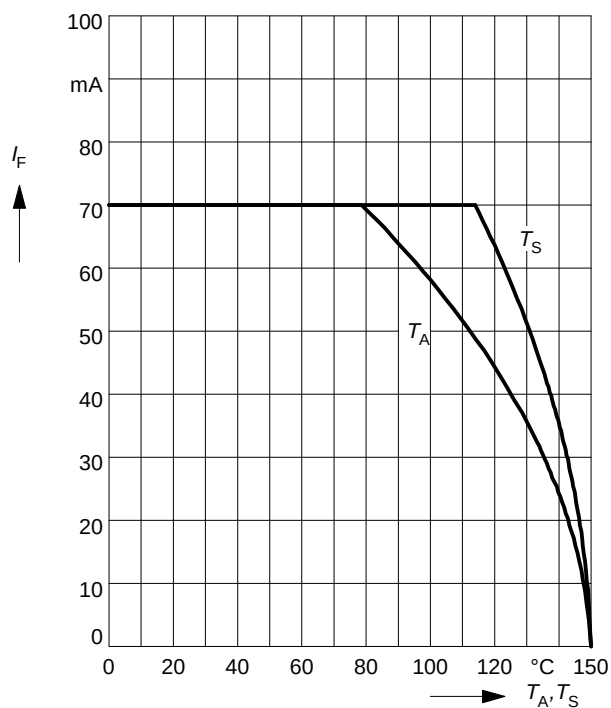
$f = 10\text{kHz}$



Forward Current $I_F = f(T_A^*; T_S)$

* mounted on PCB 40x40x1.5mm/6cm²Cu

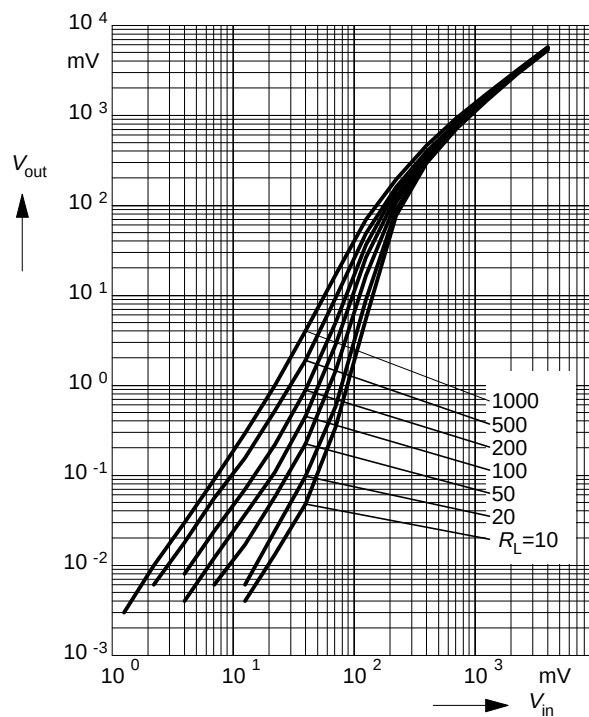
I_F per diode



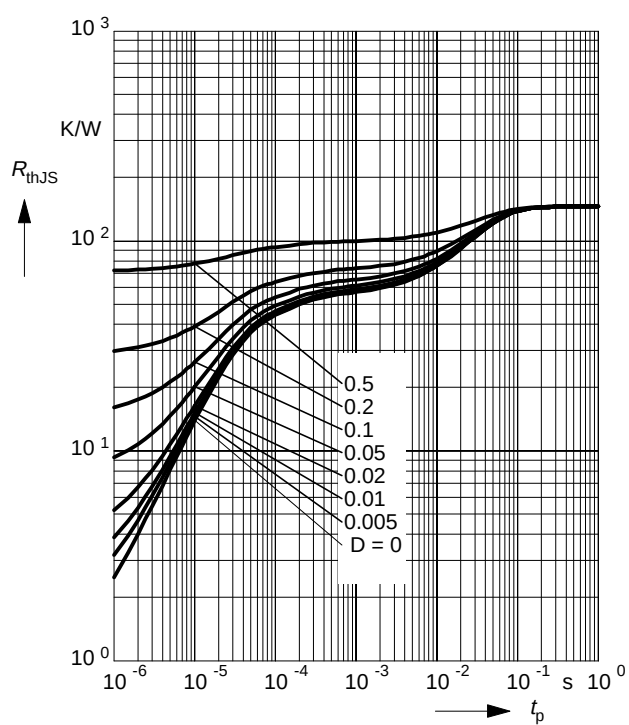
Rectifier Voltage vs. Input Voltage

$f = 900\text{MHz}$

$R_L = \text{parameter in k}\Omega$



Permissible Pulse Load $R_{thJS} = f(t_p)$



Permissible Pulse Load $I_{Fmax}/I_{FDC} = f(t_p)$

